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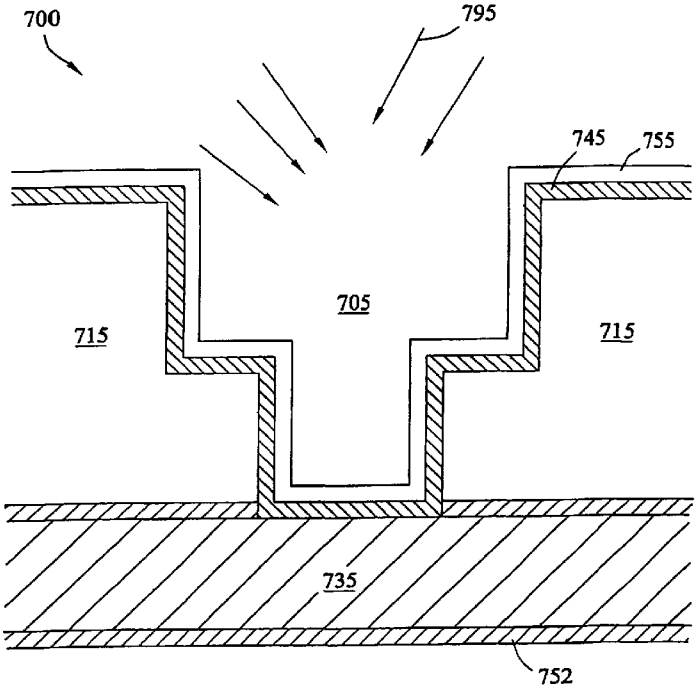
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(54) Title: METHOD OF IMPLANTATION AFTER COPPER SEED DEPOSITION



(57) Abstract: A method of fabricating an integrated circuit can include forming a barrier layer along lateral side walls and a bottom of a via aperture, forming a seed layer proximate and conformal to the barrier layer, and forming an implanted layer proximate and conformal to the barrier layer and the seed layer. The via aperture is configured to receive a via material that electrically connects a first conductive layer and a second conductive layer.

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